

U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.		Serial No.	
				M-11466-8C US		10/027,592	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicants:			
				Tony P. Chiang et al.			
				Filing Date		Group	
				December 19, 2001		Unknown	
U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EF	AI	T. P. Chiang et al., "Ion-induced chemical vapor deposition of high purity Cu films at room temperature using a microwave discharge H atom beam source", <u>J.Vac.Sci.Technol. A 15(5)</u> , Sep/Oct 1997, pp 2677-2686.					
EF	AJ	T. P. Chiang et al. "Surfaced kinetic study of ion-induced chemical vapor deposition of copper for focused ion beam applications", <u>J.Vac.Sci.Technol. A 15(6)</u> , Nov/Dec 1997, pp 3104-3114.					
EF	AK	K. A. Ashtiani et al., "A New Hollow-Cathode Magnetron Source for 0.10 μ m Copper Applications", <u>Novellus Systems, Inc.</u> , San Jose, CA, <i>date unknown</i> , 3 pgs.					
EF	AL	X. Chen et al., "Low temperature plasma-promoted chemical vapor deposition of tantalum from tantalum pentabromide for copper metallization", <u>J.Vac.Sci.Technol. B 16(5)</u> , Sep/Oct 1998, pp 2887-2890.					
EF	AM	X. Chen et al., "Low temperature plasma-assisted chemical vapor deposition of tantalum nitride from tantalum pentabromide for copper metallization", <u>J.Vac.Sci.Technol. B 17(1)</u> , Jan/Feb 1999, pp 182-185.					
EF	AN	P. Mårtensson, "Atomic Layer Epitaxy of Copper", <u>Comprehensive Summaries of Uppsala Dissertations from the Faculty of Science and Technology 421</u> , 1999, pp. 1-45, Acta Universitatis Upsaliensis, Uppsala, Sweden.					
EF	AO	P. Mårtensson et al., "Atomic Layer Epitaxy of Copper on Tantalum", <u>Chemical Vapor Deposition</u> , 1997, pp. 45-50, vol. 3, no. 1.					
EF	AP	M. Ritala et al., "Controlled Growth of TaN, Ta ₃ N ₅ , and TaO _x N _y Thin Films by Atomic Layer Deposition", <u>Chemical Materials</u> , vol. 11, no. 7, 1999, American Chemical Society, pp 1712-1718.					
Examiner		Date Considered					
E. P. Chiang		9/19/02					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.							